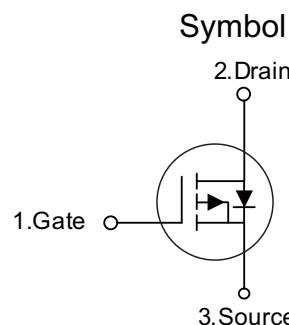


■ PRODUCT CHARACTERISTICS

V _{DSS}	-30 V
R _{D(S)} (ON)-Typ (at V _{GS} =-10V)	23 mΩ
R _{D(S)} (ON)-Typ (at V _{GS} =-4.5V)	33 mΩ
I _D	-10A

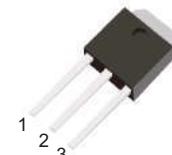


■ APPLICATIONS

LCD TV Appliances
 LCDM Appliances
 High power inerrter system



TO-252



TO-251

■ FEATURES

Surface-mounted package
 Advanced trench cell design

■ ORDER INFORMATION

Order codes		Package	Packing
Halogen-Free	Halogen		
N/A	MOT10P03D	TO-252	2500 pieces /Reel
N/A	MOT10P03C	TO-251	70 pieces/Tube

 ■ ABSOLUTE MAXIMUM RATINGS (T_C =25°C, unless otherwise specified)

Parameter		Symbol	Value	Unit
Drain-Source Voltage		V _{DSS}	-30	V
Gate -Source Voltage		V _{GSS}	±20	V
Continuous Drain Current	T _C =25°C	I _D	-10	A
	T _C =100°C	I _D	-6.5	A
Pulsed Drain Current		I _{DM}	-40	A
Single Pulsed Avalanche Energy		E _{AS}	72	mJ
Power Dissipation		P _D	30	W
Thermal Resistance, Junction to Case		R _{θJC}	4.1	°C /W
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to + 150	°C

■ ELECTRICAL CHARACTERISTICS($T_J = 25^\circ\text{C}$, unless otherwise noted)

Parameter	Symbol	Test condition	Min	Typ	Max	Unit
Off characteristics						
Drain-Source Breakdown Voltage	$V_{(\text{BR})\text{DSS}}$	$V_{GS} = 0V, I_D = -250\mu\text{A}$	-30	-	-	V
Zero Gate Voltage Drain Voltage	I_{DSS}	$V_{DS} = -30V, V_{GS} = 0V$	-	-	-1	μA
Gate to Body Leakage Current	I_{GSS}	$V_{DS} = 0V, V_{GS} = \pm 20V$	-	-	± 100	nA
On characteristics						
Gate Threshold Voltage	$V_{GS(\text{th})}$	$V_{DS} = V_{GS}, I_D = -250\mu\text{A}$	-1.0	-1.5	-2.5	V
Static Drain-Source on-Resistance	$R_{DS(\text{on})}$	$V_{GS} = -10V, I_D = -5\text{A}$	-	23	30	$\text{m}\Omega$
		$V_{GS} = -4.5V, I_D = -5\text{A}$	-	33	45	$\text{m}\Omega$
Dynamic characteristics						
Input Capacitance	C_{iss}	$V_{DS} = -00V, V_{GS} = 0V, f = 1.0\text{MHz}$	-	830	-	pF
Output Capacitance	C_{oss}		-	99	-	pF
Reverse Transfer Capacitance	C_{rss}		-	86	-	pF
Total Gate Charge	Q_g	$V_{DD} = -15V, I_D = -5\text{A}, V_{GS} = -10V$	-	23	-	nC
Gate-Source Charge	Q_{gs}		-	4	-	nC
Gate-Drain("Miller") Charge	Q_{gd}		-	5	-	nC
Switching characteristics						
Turn-on Delay Time	$t_{d(on)}$	$V_{DD} = -15V, I_D = -5\text{A}, V_{GS} = -10V, R_{GEN} = 3\Omega$	-	4	-	ns
Turn-on Riss Time	t_r		-	3	-	ns
Turn-off Delay Time	$t_{d(off)}$		-	60	-	ns
Turn-off Fall Time	t_f		-	50	-	ns
Drain-source diode characteristics						
Continuous Drain to Source	I_s		-	-	-10	A
Pulsed Drain to Source	I_{SM}		-	-	-40	A
Drain to Source Diode Forward Voltage	V_{SD}	$V_{GS} = 0V, I_s = -10\text{A}$	-	-	-1.2	V

Dynamic Characteristics

C_{iss}	Input Capacitance	$V_{GS} = 0V, V_{DS} = -15V, f = 1\text{MHz}$	-	1267	-	pF
C_{oss}	Output Capacitance		-	166	-	pF
C_{rss}	Reverse Transfer Capacitance		-	126	-	pF
Q_g	Total Gate Charge	$V_{GS} = 0 \text{ to } -10V, V_{DS} = -15V, I_D = -5\text{A}$	-	23	-	nC
Q_{gs}	Gate Source Charge		-	4	-	nC
Q_{gd}	Gate Drain("Miller") Charge		-	5	-	nC

Switching Characteristics

$t_{d(on)}$	Turn-On DelayTime	$V_{GS} = -10V, V_{DD} = -15V, I_D = -5A, R_{GEN} = 3\Omega$	-	4	-	ns
t_r	Turn-On Rise Time		-	3	-	ns
$t_{d(off)}$	Turn-Off DelayTime		-	60	-	ns
t_f	Turn-Off Fall Time		-	50	-	ns

Drain-Source Diode Characteristics and Max Ratings

I_s	Maximum Continuous Drain to Source Diode Forward Current	-	-	-12	A	
I_{SM}	Maximum Pulsed Drain to Source Diode Forward Current	-	-	-48	A	
V_{SD}	Drain to Source Diode Forward Voltage	$V_{GS} = 0V, I_s = -12\text{A}$	-	-	-1.2	V
trr	Body Diode Reverse Recovery Time	$I_F = -5\text{A}, di/dt = 100\text{A/us}$	-	12	-	ns
Qrr	Body Diode Reverse Recovery Charge		-	4	-	nC

Notes: 1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature.

■ TYPICAL CHARACTERISTICS

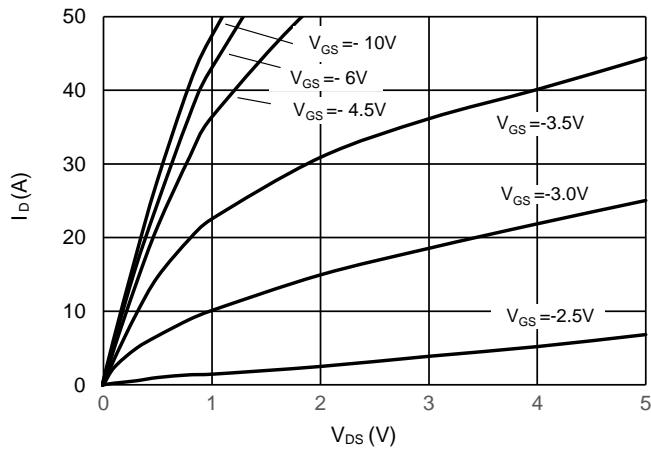


Figure 1: Output characteristics

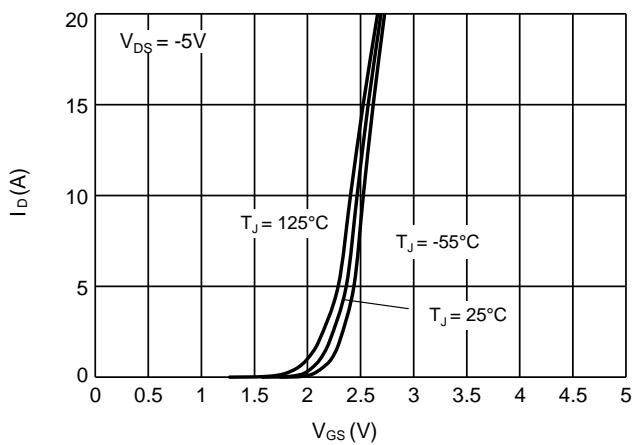


Figure 2: Typical transfer characteristics

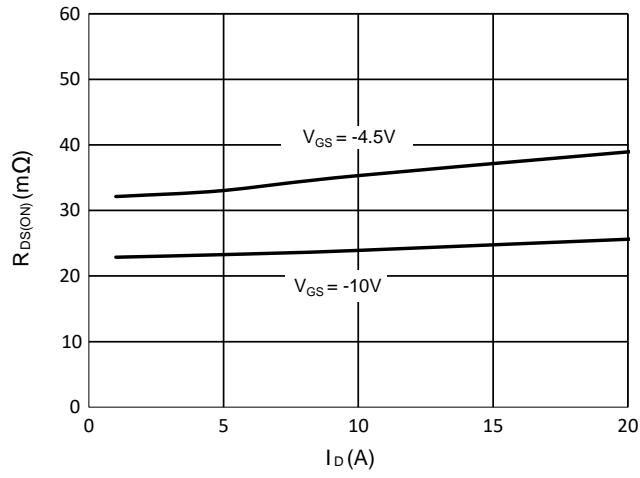


Figure 3: On-resistance vs. drain current

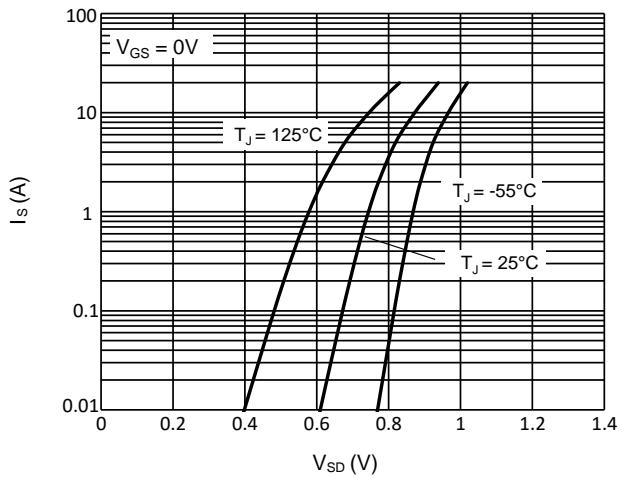


Figure 4: Body diode characteristics

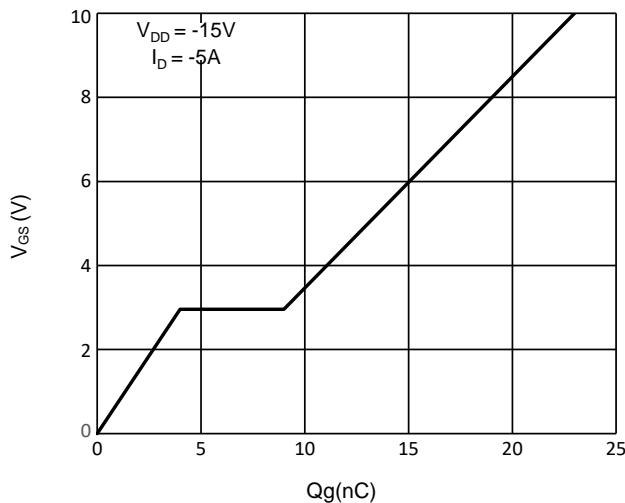


Figure 5: Gate charge characteristics

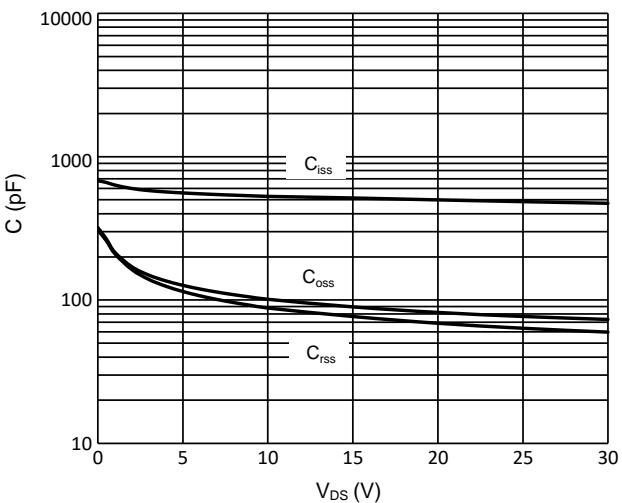


Figure 6: Capacitance characteristics

■ TYPICAL CHARACTERISTICS(Cont.)

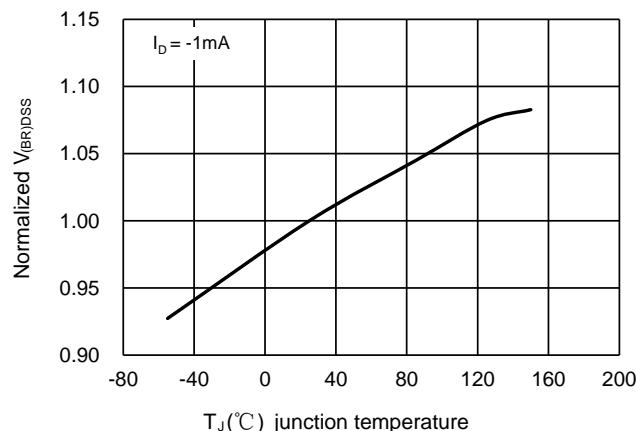


Figure 7: Normalized breakdown voltage vs junction temperature

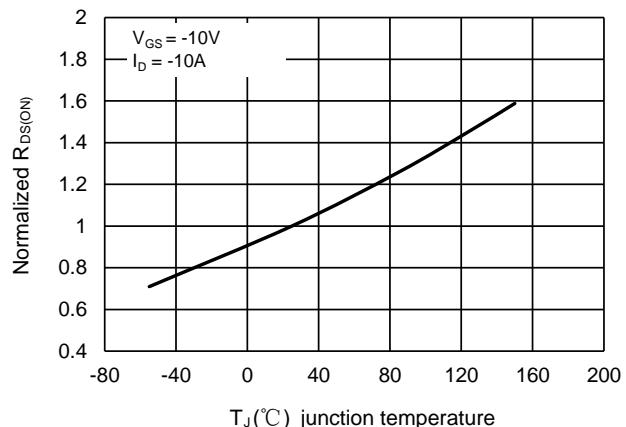


Figure 8: Normalized on-resistance vs junction temperature

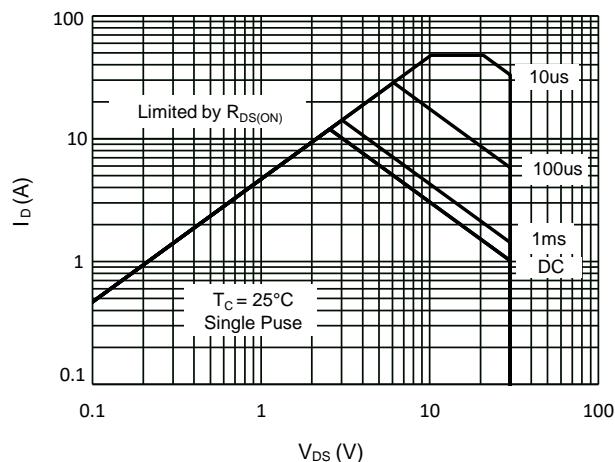


Figure 9: Maximum safe operating area vs junction temperature

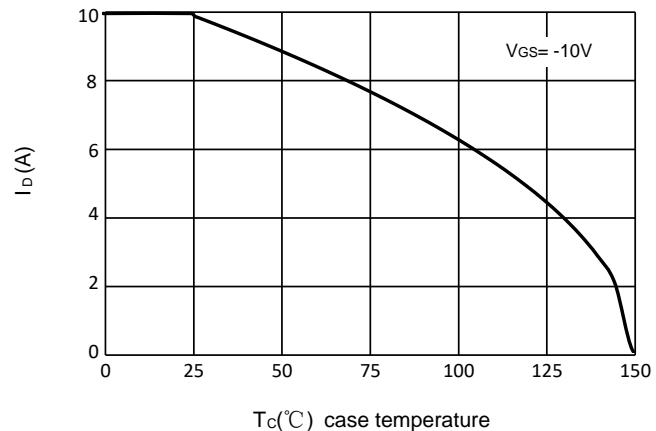
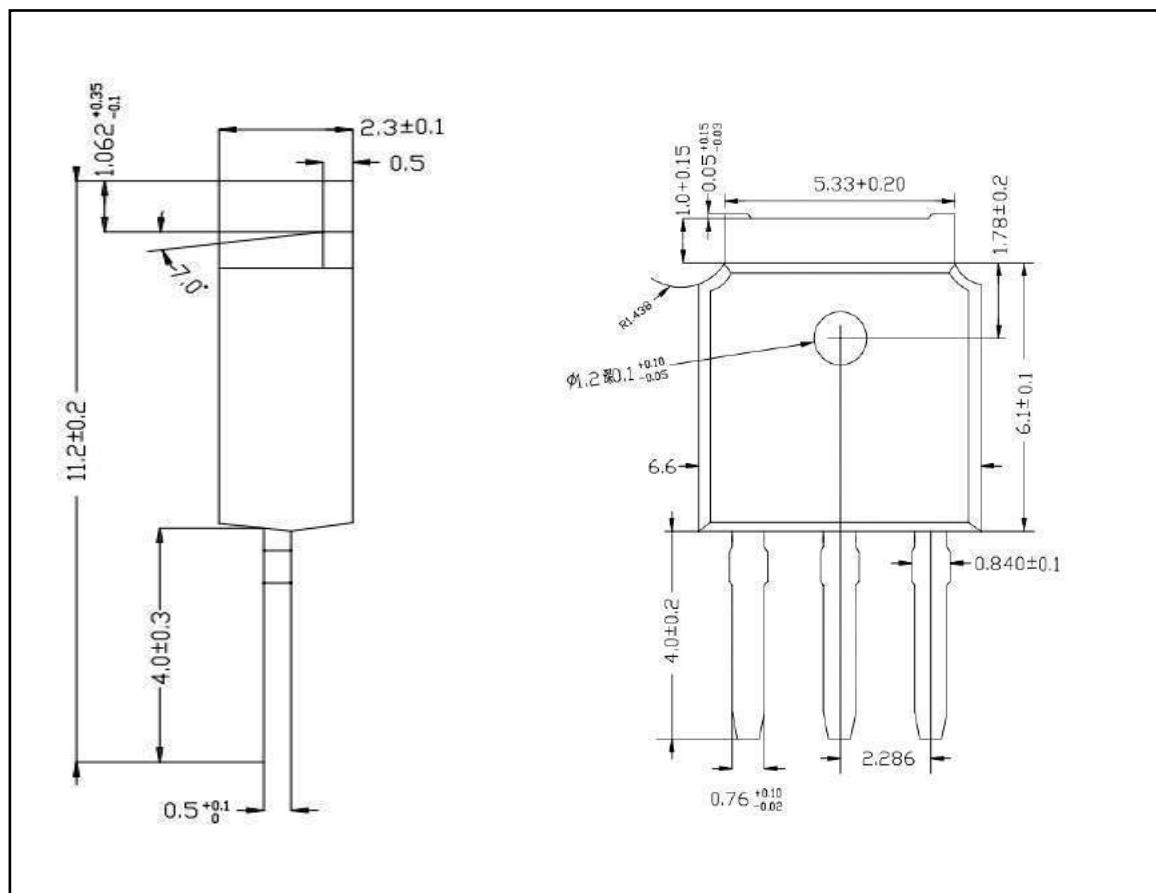


Figure 10: Maximum continuous drain current vs. case temperature

■ TO-252 PACKAGE OUTLINE DIMENSIONS



■ TO-252 PACKAGE OUTLINE DIMENSIONS

